

Part Number

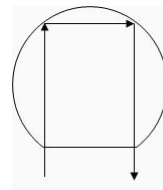
Customer

Category	Parameter	Specification	Measurement Method
OverallWafer	1.0	Diameter	100.00 +/- 0.50 mm
	2.0	Primary Flat Orientation	{110} +/- 1 degree
	3.0	Primary Flat Length	32.50 +/- 1.50 mm
	4.0	Secondary Flat Orientation	none
	5.0	Overall Thickness	404.00 +/- 10.00 μ m
	6.0	Total Thickness Variation (TTV)	<2.00
	7.0	Bow	<50.00 μ m
	8.0	Warp	<50.00 μ m
	9.0	Edge Chips	0
	10.0	Edge Exclusion	5mm
HandleSilicon	11.0	Handle Growth Method	FZ
	12.0	Handle Orientation	{100} +/- 0.2 degree
	13.0	Handle Thickness	350.00 +/- 5.00 μ m
	14.0	Handle Doping Type	P
	15.0	Handle Dopant	Boron
	16.0	Handle Resistivity	> 1000 Ohmcm
	17.0	Backside Finish	Polished with "2um" oxide / lasermarking: 2.7mm from primary flat / fontsize 2.0mm
BuriedOxide	18.0	Oxide Type	Thermal
	19.0	Oxide Thickness	20,000.00 +/- 1,000.00 A
	20.0	Oxide formed on	1um Handle Wafer / 1um Device wafer
DeviceSilicon	21.0	Device Growth Method	CZ
	22.0	Device Orientation	{100} +/- 0.2 degree
	23.0	Nominal Thickness	50.00 +/- 1.00 μ m
	24.0	Distance to device silicon edge from wafer edge	<= 1.5mm
	25.0	Device Doping Type	P
	26.0	Device Dopant	Boron
	27.0	Device Resistivity	0.01 - 0.02 Ohmcm
	41.0	Voids	none
	42.0	Scratches	none
	43.0	Haze	none

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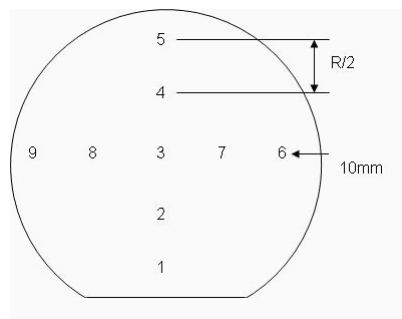
Shipping Details	Wafer per box :	Max 25
	Packaging :	Taped Polypropylene Wafer Box Empak, Ultrapak, 100.00mm Antistatic Double Bagging
	Lot Shipment Data	Device Thickness Bow / Warp Data Handle and SOI Thickness



Explanatory Notes 1. Microscope inspection performed using microscope scan as below. 5x objective.

2. All bright light inspections performed exclude all wafer area outside the edge exclusion defined in Overall Wafer, Edge Exclusion. High intensity bright lamp inspection as per ASTM F523.

3. 9 point measurement are as shown in the diagram below:



Additional Information